



FIS920030239US1 (TLT)  
Steven W. Bedell, et al.

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FIG. 1

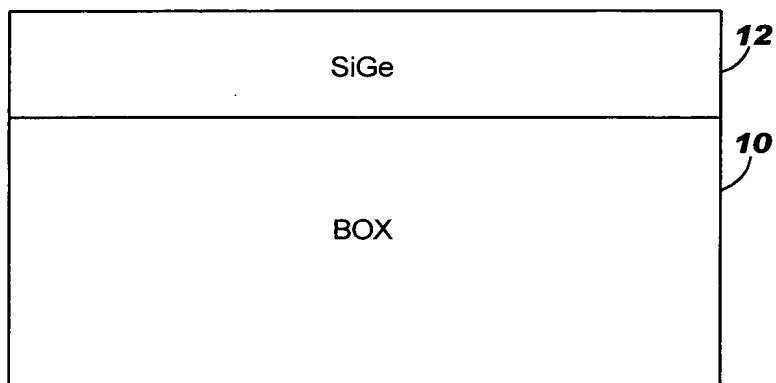
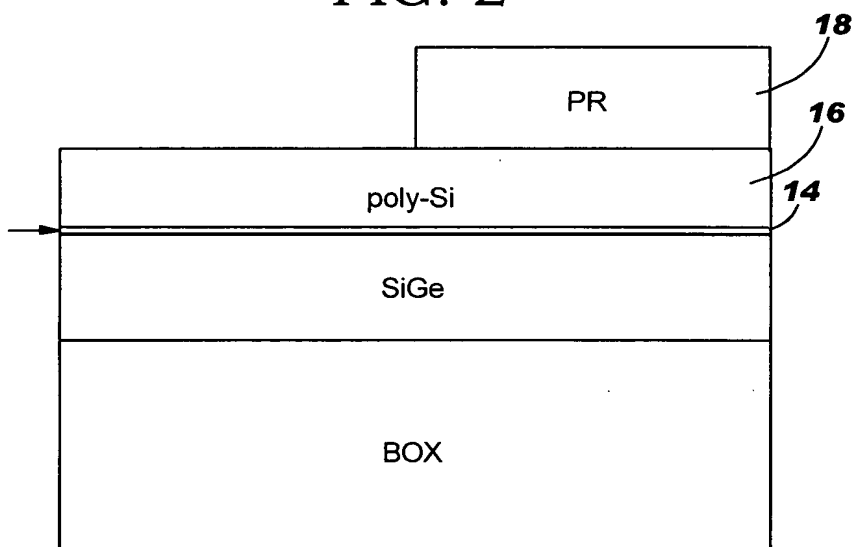


FIG. 2



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FIG. 3

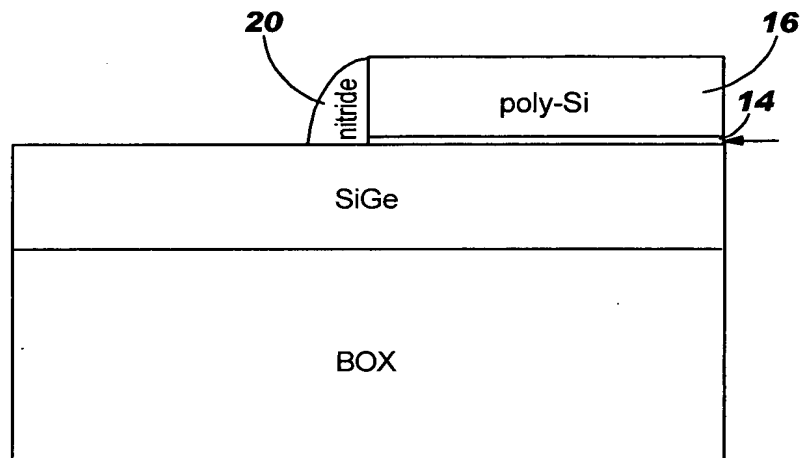
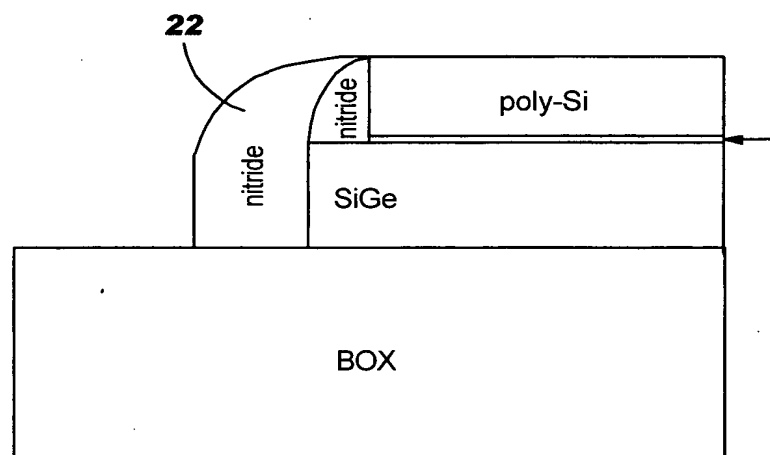


FIG. 4



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FIG. 5

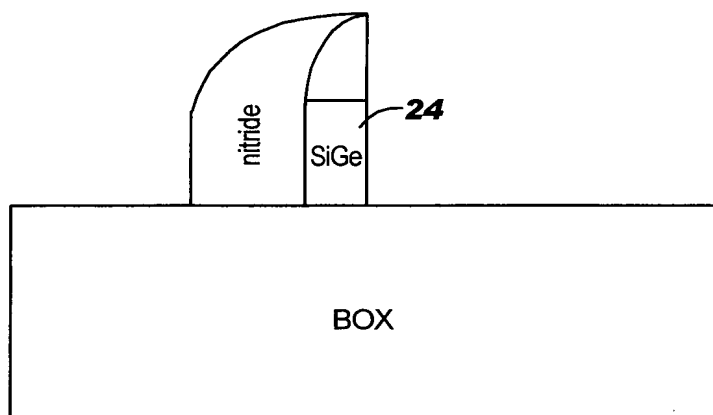
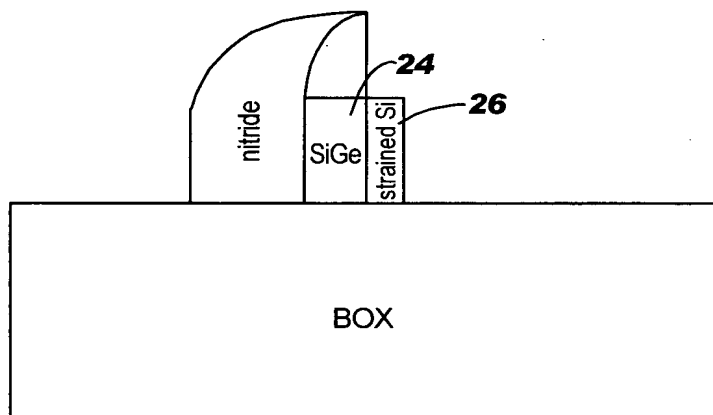


FIG. 6



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FIG. 7

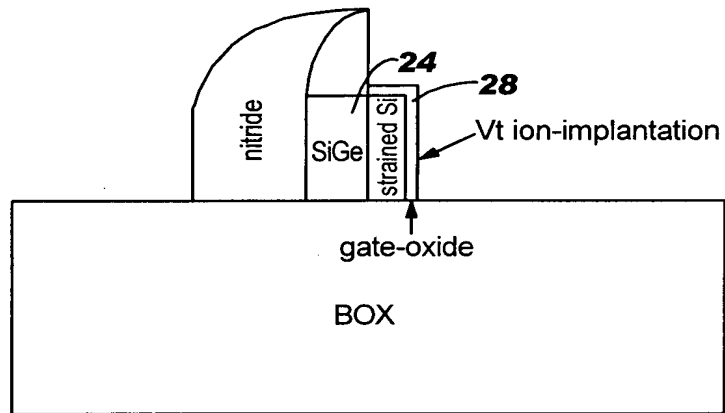
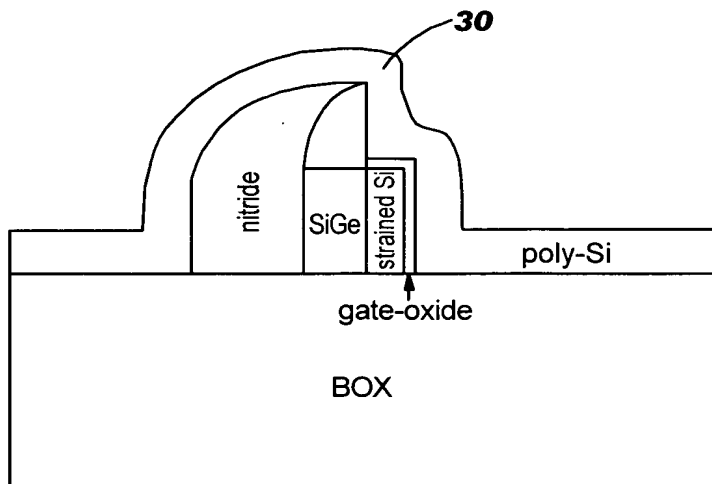


FIG. 8



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FIG. 9

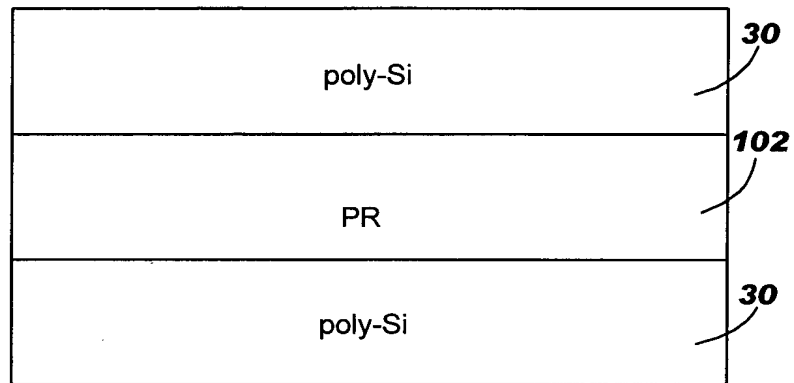
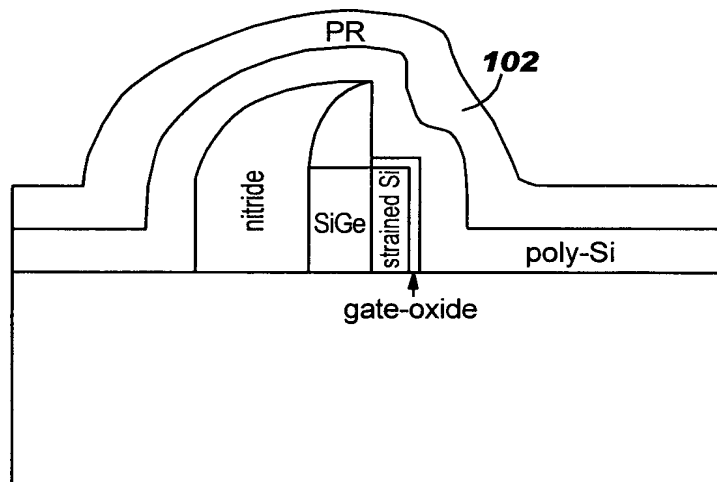
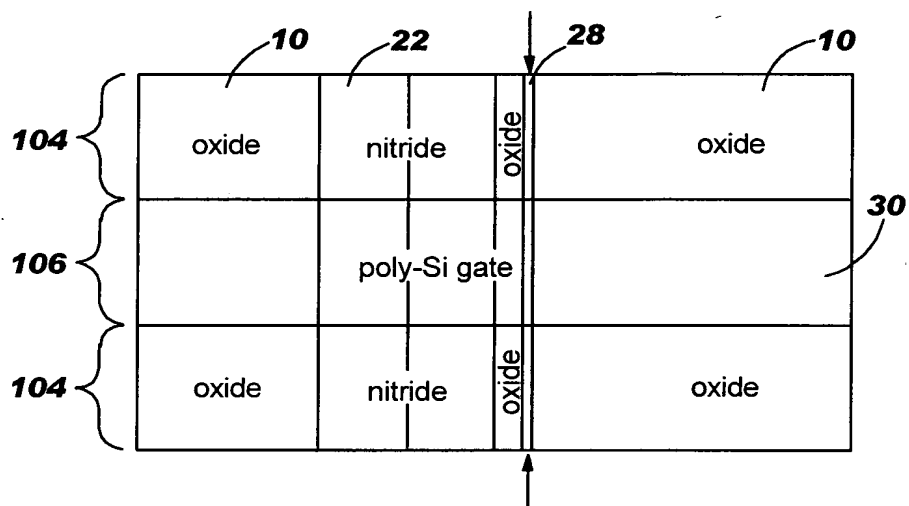


FIG. 10



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FIG. 11



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FIG. 12

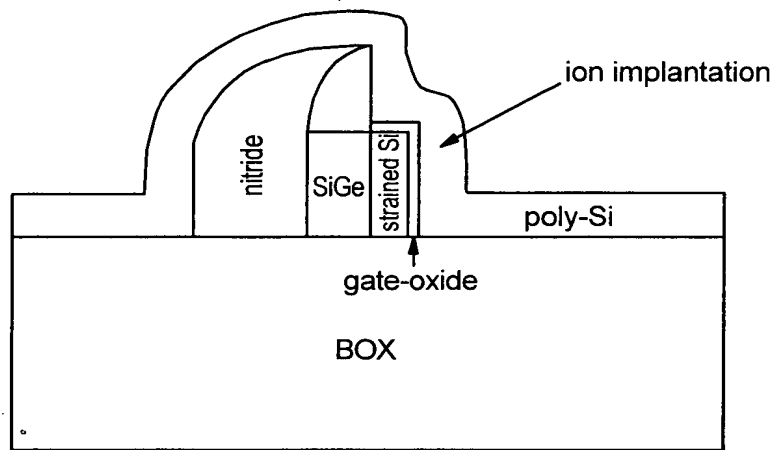


FIG. 13

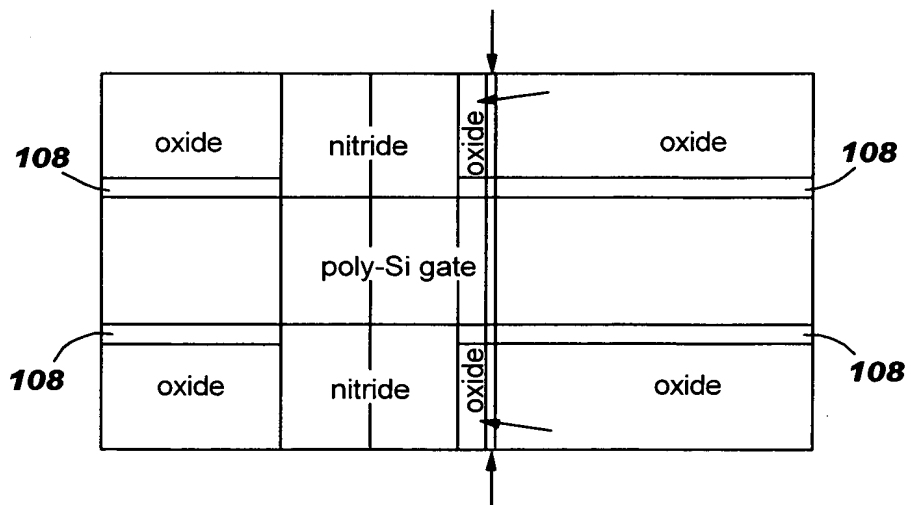


Diagram 108 shows a cross-sectional view of a semiconductor device. The structure consists of a substrate labeled "BOX" (Buried Oxide) at the bottom. Above the BOX is a layer of "gate-oxide". On top of the gate-oxide is a "poly-Si" (polysilicon) layer. Within the poly-Si layer, there is a region labeled "strained Si". Above the strained Si is a layer of "SiGe" (Silicon Germanium). The entire structure is covered by a "nitride" layer. A label "108" with an arrow points to the nitride layer.



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FIG. 16

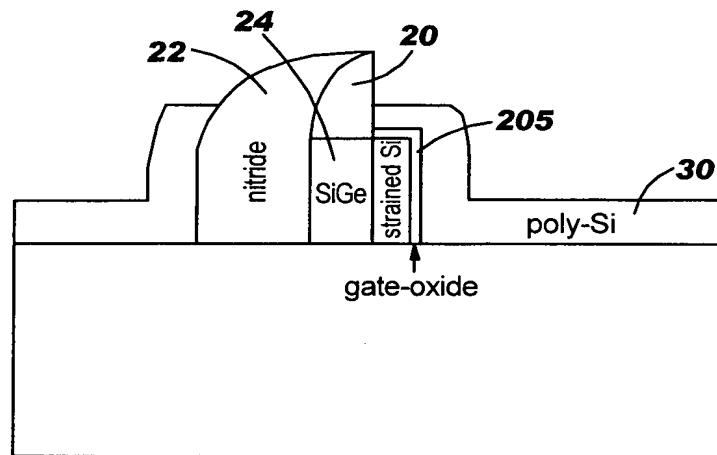
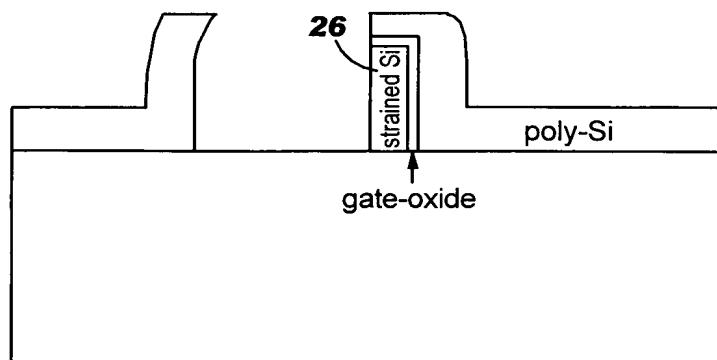


FIG. 17



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FIG. 18

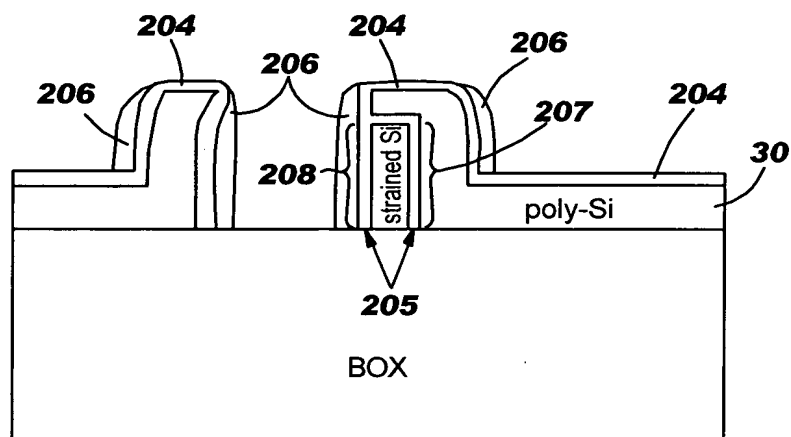


FIG. 19

